

CURRENT 15 Ampere
VOLTAGE RANG 1200 Volts

ASE15N120

General Description

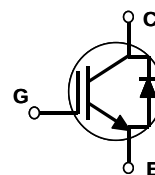
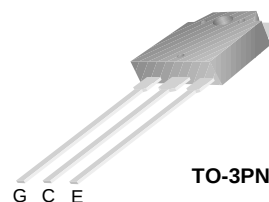
Employing NPT technology, Fairchild's AND series of IGBTs provides low conduction and switching losses. The AND series offers solutions for applications such as induction heating (IH), motor control, general purpose inverters and uninterruptible power supplies (UPS).

Features

- High speed switching
- Low saturation voltage : $V_{CE(sat)} = 2.4\text{ V @ } I_C = 15\text{ A}$
- High input impedance
- CO-PAK, IGBT with FRD : $t_{rr} = 210\text{ ns (typ.)}$

Applications

Induction Heating, UPS, AC & DC motor controls and general purpose inverters.



Absolute Maximum Ratings

$T_C = 25^\circ\text{C}$ unless otherwise noted

Symbol	Description	ASE15N120	Units
V_{CES}	Collector-Emitter Voltage	1200	V
V_{GES}	Gate-Emitter Voltage	± 20	V
I_C	Collector Current @ $T_C = 25^\circ\text{C}$	24	A
	Collector Current @ $T_C = 100^\circ\text{C}$	15	A
$I_{CM(1)}$	Pulsed Collector Current	45	A
I_F	Diode Continuous Forward Current @ $T_C = 100^\circ\text{C}$	15	A
I_{FM}	Diode Maximum Forward Current	45	A
P_D	Maximum Power Dissipation @ $T_C = 25^\circ\text{C}$	200	W
	Maximum Power Dissipation @ $T_C = 100^\circ\text{C}$	80	W
T_J	Operating Junction Temperature	-55 to +150	$^\circ\text{C}$
T_{stg}	Storage Temperature Range	-55 to +150	$^\circ\text{C}$
T_L	Maximum Lead Temp. for soldering Purposes, 1/8" from case for 5 seconds	300	$^\circ\text{C}$

Notes :

(1) Repetitive rating : Pulse width limited by max. junction temperature

Thermal Characteristics

Symbol	Parameter	Typ.	Max.	Units
$R_{\theta JC}$ (IGBT)	Thermal Resistance, Junction-to-Case	--	0.63	$^\circ\text{C/W}$
$R_{\theta JC}$ (DIODE)	Thermal Resistance, Junction-to-Case	--	2.88	$^\circ\text{C/W}$
$R_{\theta JA}$	Thermal Resistance, Junction-to-Ambient	--	40	$^\circ\text{C/W}$

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Electrical Characteristics of the IGBT T_C = 25°C unless otherwise noted

Symbol	Parameter	Test Conditions	Min.	Typ.	Max.	Units
Off Characteristics						
BV _{CES}	Collector-Emitter Breakdown Voltage	V _{GE} = 0V, I _C = 3mA	1200	--	--	V
$\Delta B_{V_{CES}} / \Delta T_J$	Temperature Coefficient of Breakdown Voltage	V _{GE} = 0V, I _C = 3mA	--	0.6	--	V/°C
I _{CES}	Collector Cut-Off Current	V _{CE} = V _{CES} , V _{GE} = 0V	--	--	3	mA
I _{GES}	G-E Leakage Current	V _{GE} = V _{GES} , V _{CE} = 0V	--	--	± 100	nA

On Characteristics

V _{GE(th)}	G-E Threshold Voltage	I _C = 15mA, V _{CE} = V _{GE}	3.5	5.5	7.5	V
V _{CE(sat)}	Collector to Emitter Saturation Voltage	I _C = 15A, V _{GE} = 15V	--	2.4	3.2	V
		I _C = 15A, V _{GE} = 15V, T _C = 125°C	--	2.9	--	V
		I _C = 24A, V _{GE} = 15V	--	3.0	--	V

Dynamic Characteristics

C _{ies}	Input Capacitance	V _{CE} = 30V, V _{GE} = 0V, f = 1MHz	--	1150	--	pF
C _{oes}	Output Capacitance		--	120	--	pF
C _{res}	Reverse Transfer Capacitance		--	56	--	pF

Switching Characteristics

t _{d(on)}	Turn-On Delay Time	V _{CC} = 600 V, I _C = 15A, R _G = 20Ω, V _{GE} = 15V, Inductive Load, T _C = 25°C	--	90	--	ns
t _r	Rise Time		--	70	--	ns
t _{d(off)}	Turn-Off Delay Time		--	310	--	ns
t _f	Fall Time		--	60	120	ns
E _{on}	Turn-On Switching Loss		--	3.27	4.9	mJ
E _{off}	Turn-Off Switching Loss	V _{CC} = 600 V, I _C = 15A, R _G = 20Ω, V _{GE} = 15V, Inductive Load, T _C = 125°C	--	0.6	0.9	mJ
E _{ts}	Total Switching Loss		--	3.68	5.8	mJ
t _{d(on)}	Turn-On Delay Time		--	80	--	ns
t _r	Rise Time		--	60	--	ns
t _{d(off)}	Turn-Off Delay Time		--	310	--	ns
t _f	Fall Time		--	50	--	ns
E _{on}	Turn-On Switching Loss	V _{CE} = 600 V, I _C = 15A, V _{GE} = 15V	--	3.41	--	mJ
E _{off}	Turn-Off Switching Loss		--	0.84	--	mJ
E _{ts}	Total Switching Loss		--	4.25	--	mJ
Q _g	Total Gate Charge		--	120	180	nC
Q _{ge}	Gate-Emitter Charge		--	9	14	nC
Q _{gc}	Gate-Collector Charge	Measured 5mm from PKG	--	63	95	nC
L _e	Internal Emitter Inductance		--	14	--	nH

Electrical Characteristics of DIODE T_C = 25°C unless otherwise noted

Symbol	Parameter	Test Conditions		Min.	Typ.	Max.	Units
V _{FM}	Diode Forward Voltage	I _F = 15A	T _C = 25°C	--	1.7	2.7	V
			T _C = 125°C	--	1.8	--	
t _{rr}	Diode Reverse Recovery Time	I _F = 15A dI/dt = 200 A/μs	T _C = 25°C	--	210	330	ns
			T _C = 125°C	--	280	--	
I _{rr}	Diode Peak Reverse Recovery Current		T _C = 25°C	--	27	40	A
			T _C = 125°C	--	31	--	
Q _{rr}	Diode Reverse Recovery Charge		T _C = 25°C	--	2835	6600	nC
			T _C = 125°C	--	4340	--	

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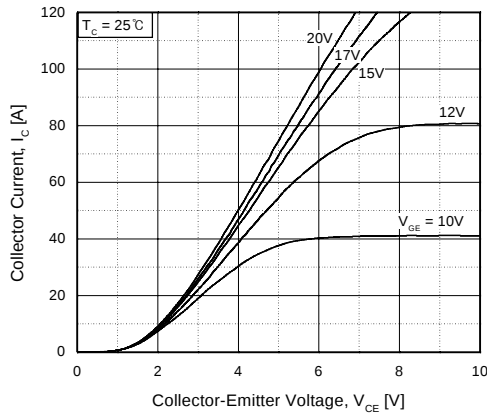


Fig 1. Typical Output Characteristics

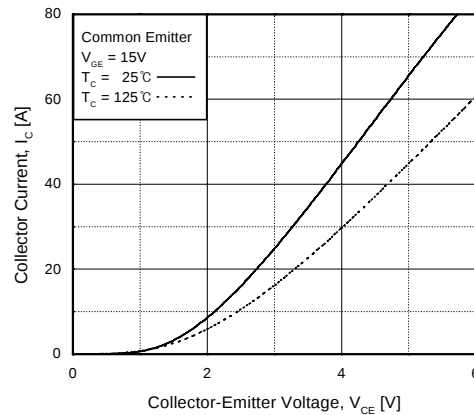


Fig 2. Typical Saturation Voltage Characteristics

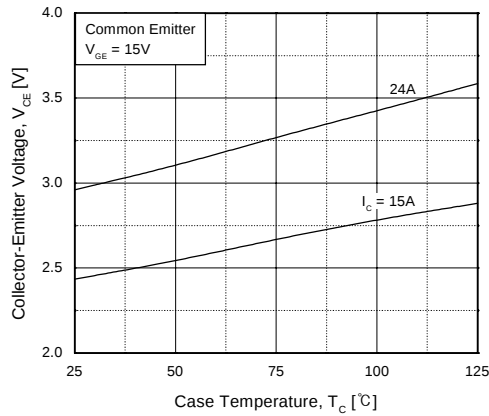


Fig 3. Saturation Voltage vs. Case Temperature at Variant Current Level

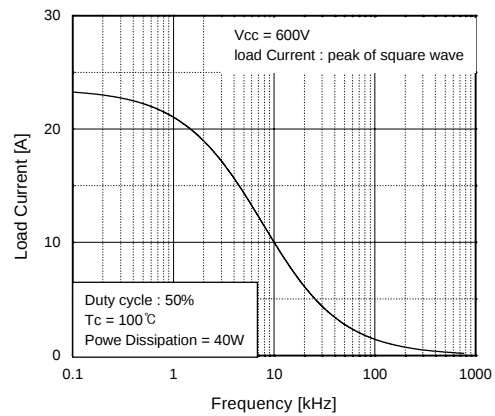


Fig 4. Load Current vs. Frequency

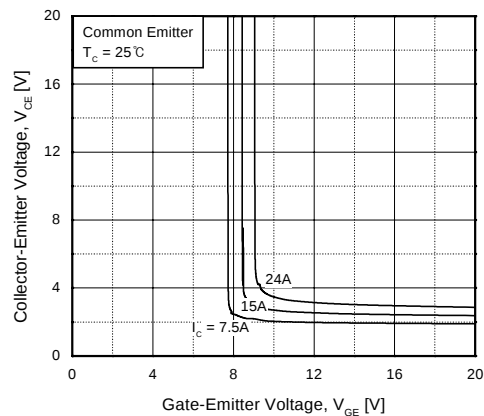


Fig 5. Saturation Voltage vs. V_{GE}

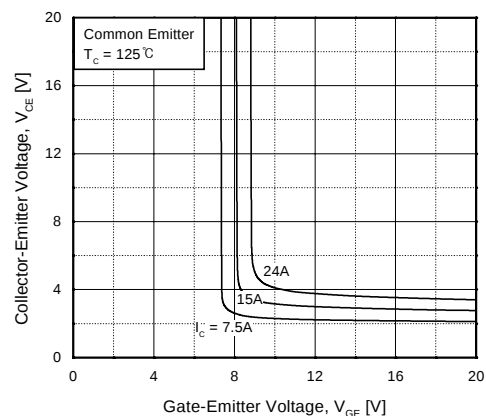


Fig 6. Saturation Voltage vs. V_{GE}

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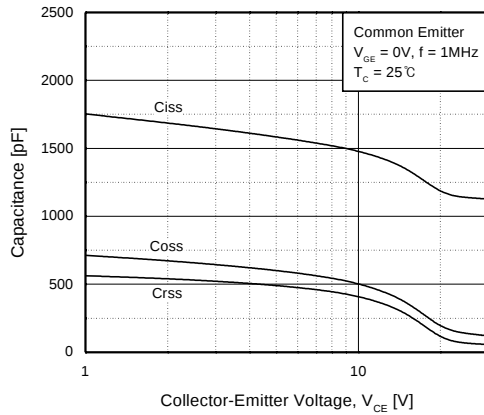


Fig 7. Capacitance Characteristics

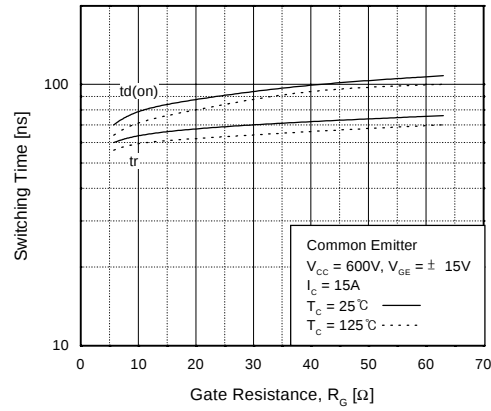


Fig 8. Turn-On Characteristics vs. Gate Resistance

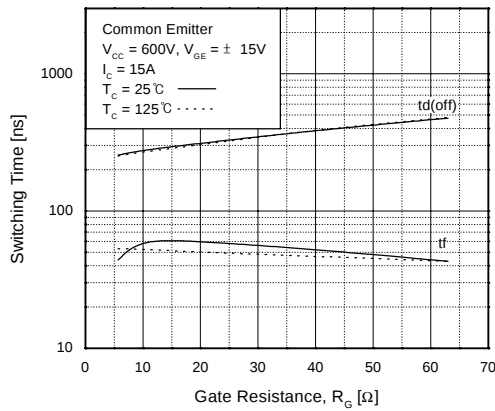


Fig 9. Turn-Off Characteristics vs. Gate Resistance

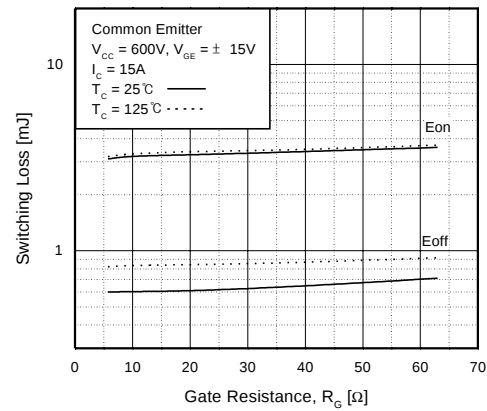


Fig 10. Switching Loss vs. Gate Resistance

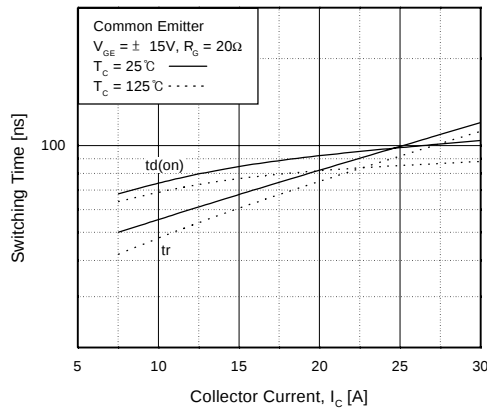


Fig 11. Turn-On Characteristics vs. Collector Current

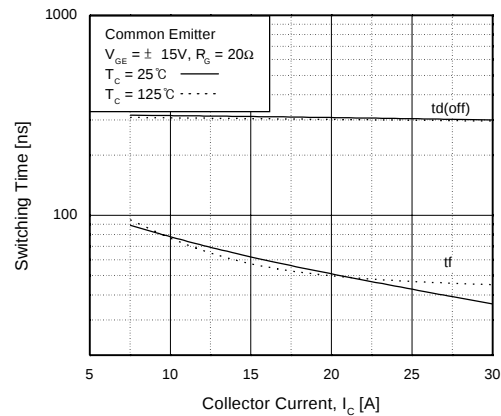


Fig 12. Turn-Off Characteristics vs. Collector Current

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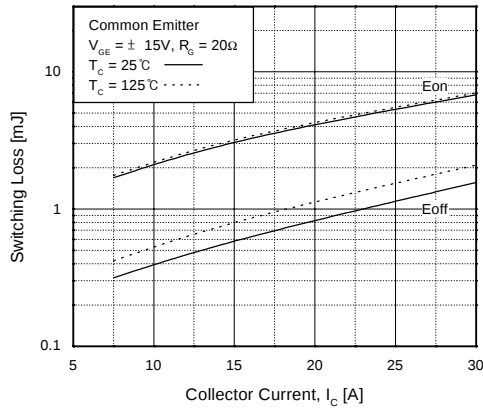


Fig 13. Switching Loss vs. Collector Current

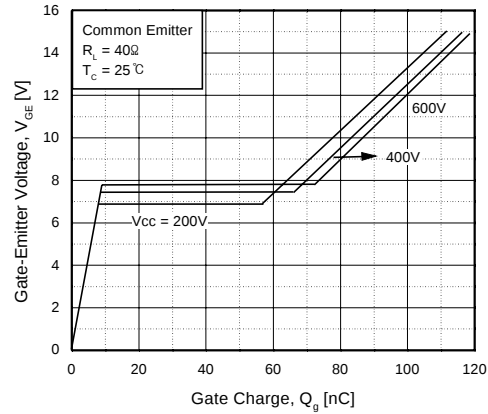


Fig 14. Gate Charge Characteristics

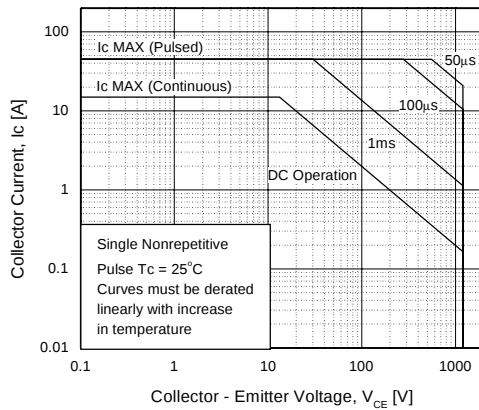


Fig 15. SOA Characteristics

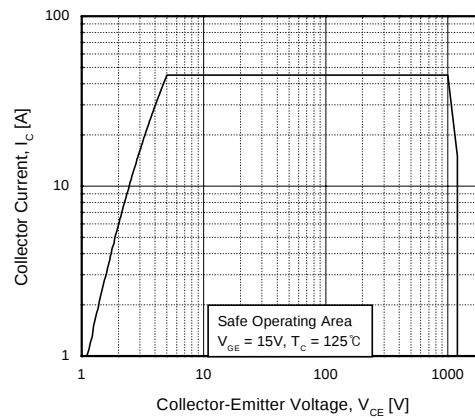


Fig 16. Turn-Off SOA

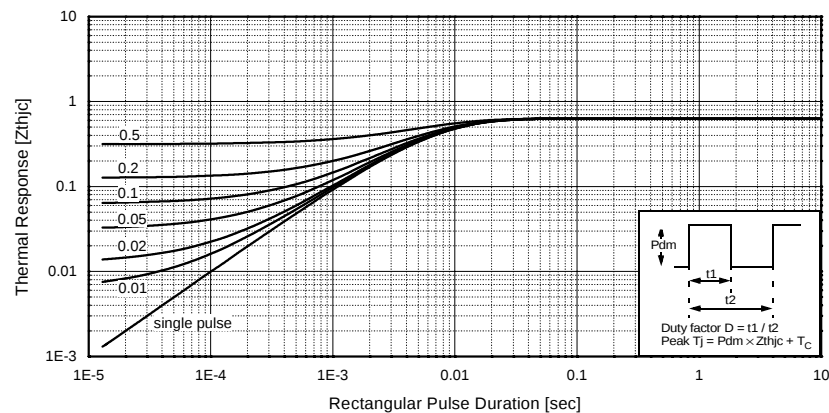


Fig 17. Transient Thermal Impedance of IGBT

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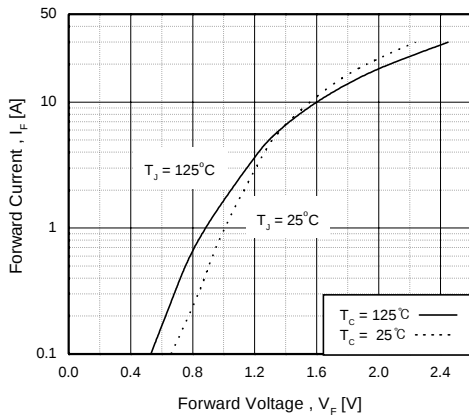


Fig 18. Forward Characteristics

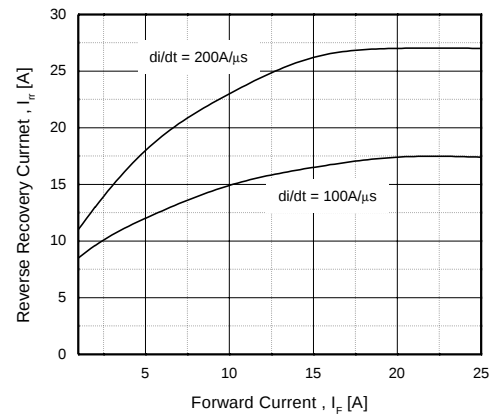


Fig 19. Reverse Recovery Current

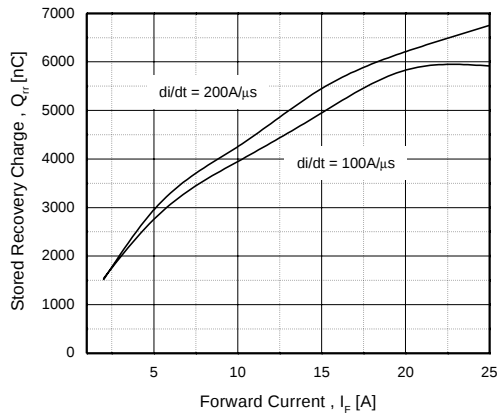


Fig 20. Stored Charge

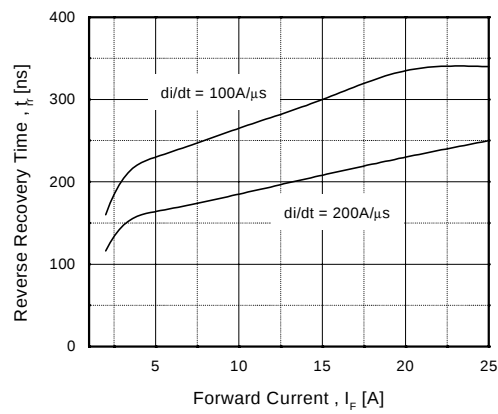


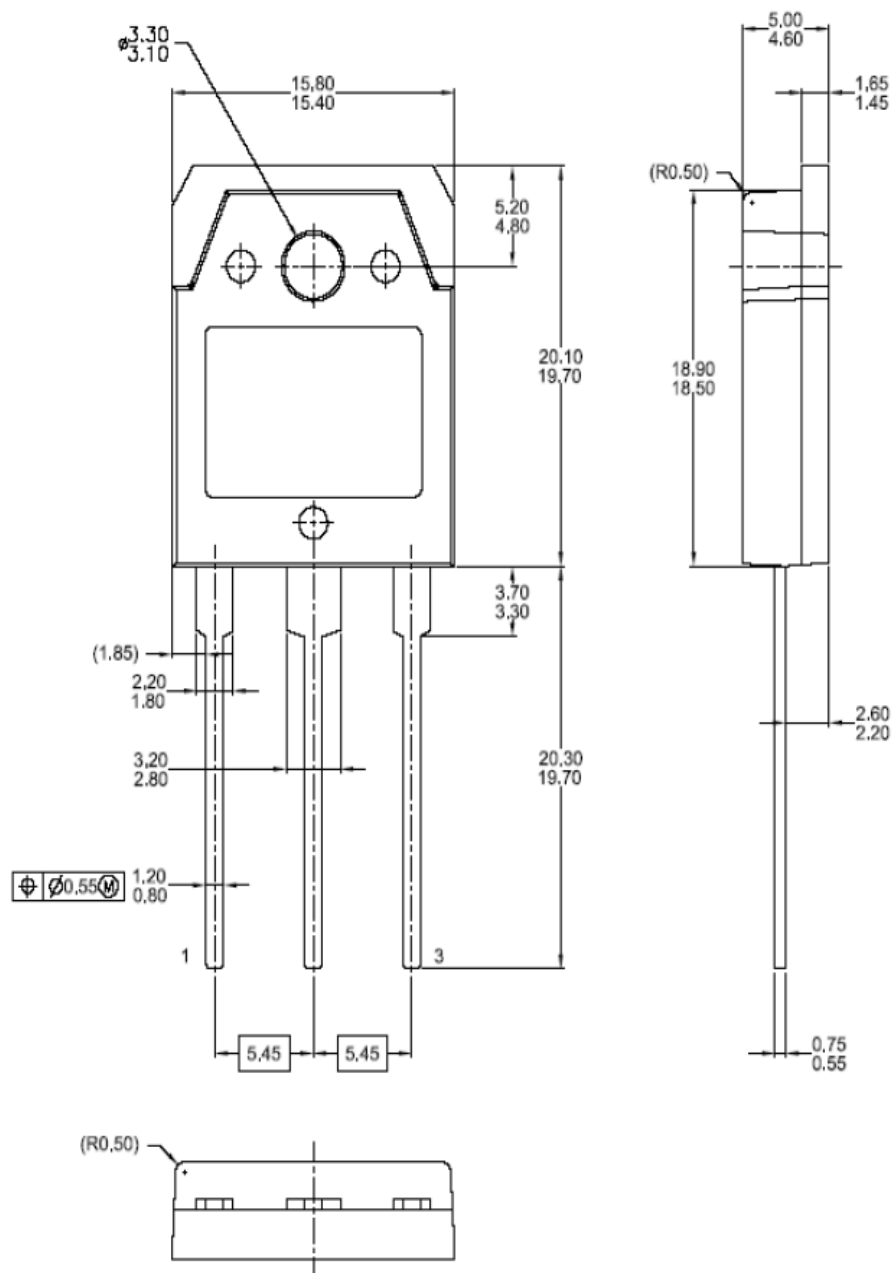
Fig 21. Reverse Recovery Time

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Mechanical Dimensions

TO-3PN



Dimensions in Millimeters